

# CORNERSTONE DESIGN GUIDELINES

## Silicon Nitride MPW #10 January 2025



**SIGN-UP DEADLINE:** 28/02/2025 **MASK SUBMISSION DEADLINE:** 26/03/2025

### 1 TERMS AND CONDITIONS AND COST

All design submissions must agree with the terms and conditions:

[www.cornerstone.sotonfab.co.uk/terms-and-conditions](http://www.cornerstone.sotonfab.co.uk/terms-and-conditions)

Under no circumstances will we accept designs without agreement with the terms.

Therefore, we strongly recommend that the terms and conditions are pre-authorised by your institution prior to the mask submission date.

A purchase order (PO) must be uploaded at the same time as submitting your mask design in order to pay the access fee, detailed in Table 1 below. Purchase orders will not be accepted via email.

Table 1 – Access cost and Delivery Time.

Design Area [mm <sup>2</sup> ]	11.47 x 15.45	Delivery Time
Access Cost with Heaters (Priority)*	£17,900	6 weeks
Access Cost without Heaters (Priority)*	£ 9,700	4 weeks
Access Cost with Heaters (Standard)*	£14,250	12 weeks
Access Cost without Heaters (Standard)*	£ 7,750	12 weeks
Access Cost for Enterprises and Academia based in UK <sup>†</sup>	50% off	12 weeks

\*Quoted prices are exclusive of VAT, import duties/customs fees, withholding taxes etc.

### †Are you a UK company or academic?

UK companies and universities may be eligible for a 50% discount on the cost of this MPW run with support from the CORNERSTONE Photonics Innovation Centre (C-PIC) (EP/Z531066/1), funded by UK Research and Innovation. Support will be provided under the Subsidy Control Act (2022) via Minimal Financial Assistance. To be eligible you will need to demonstrate the potential impact of receiving assistance against one or more of the following categories: impact on jobs and skills, access to new technology, accelerating product development. Following submission of your sign-up form, you will receive correspondence with more details of how this support will be provided. The support is only available to UK companies using CORNERSTONE for prototyping and product development.

Priority batches are designed to accelerate delivery times by utilizing expedited services for obtaining reticles, prioritizing access to cleanroom tools, working out-of-hours, and simplifying intermittent quality checks during the fabrication process, instead relying on the inherent repeatability of the lithography and etching processes. Additionally, the submitted layouts will not undergo further inspection against design rules after the submission deadline. Consequently, users opting for the priority option are required to submit designs that pass the Design Rule Check (DRC) on or before the submission deadline. The CORNERSTONE team would be grateful for the opportunity to work with you prior to the submission deadline to ensure your designs pass DRC. For more information, please visit our website: [www.cornerstone.sotonfab.co.uk/design-rules](http://www.cornerstone.sotonfab.co.uk/design-rules)

For information about setting up CORNERSTONE as a supplier to your institution, please contact [cornerstone@soton.ac.uk](mailto:cornerstone@soton.ac.uk).

## 2 DESIGN RULE CHANGES FROM PREVIOUS CALL (MPW #9)

- No change

## 3 IPKISS PROCESS DESIGN KIT

For the greatest functionality, we recommend that you use Luceda's IPKISS software to access the process design kit (PDK), after purchasing the required license. The IPKISS platform enables the automation and integration of all aspects of your photonic design flow in one tool, using one standard language. The PDK can be used in either IPKISS' Python coding environment or in the GUI of Siemens EDA L-Edit by using the IPKISS Link for Siemens EDA.

To obtain a copy of the software and a license key, please contact Luceda by sending an email to [info@lucedaphotonics.com](mailto:info@lucedaphotonics.com), specifying that you require a license for CORNERSTONE PDK usage. Luceda will contact you within 1-2 working days following the receipt of your request to provide a quote for the license. Of course, if you already have a valid license, the PDK can be accessed free of charge.

For more information, please visit [www.lucedaphotonics.com](http://www.lucedaphotonics.com).

Once you have access to the Luceda software, in order to obtain a copy of the CORNERSTONE PDK, please contact Luceda support at [info@lucedaphotonics.com](mailto:info@lucedaphotonics.com). An account will be created for you at [support.lucedaphotonics.com](http://support.lucedaphotonics.com) for any technical support on Luceda's IPKISS software or the CORNERSTONE PDK implementation.

We also have a library of building blocks available for download in .gdsII format.

## 4 PROCESS FLOW

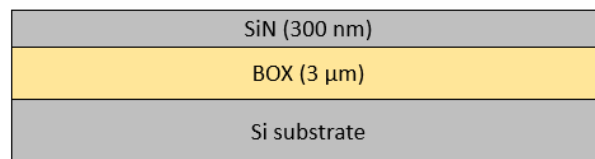
For this call, the patterns will be processed on a single-side polished SiN-on-Insulator (SiNOI) wafer, with the following nominal parameters:

- Crystalline silicon (Si) substrate
- Thermal silica (SiO<sub>2</sub>) Buried OXide (BOX) layer with a thickness  $h_{\text{BOX}} = 3 \mu\text{m}$
- LPCVD Silicon nitride (SiN) core layer  $h_{\text{wg}} = 300 \text{ nm} \pm 15 \text{ nm}$

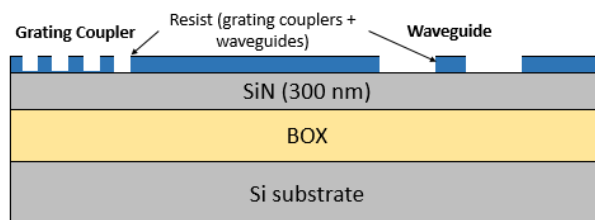
We will offer one silicon nitride etch process: 1) a full silicon nitride etch to the BOX layer. We will offer a  $2 \mu\text{m} \pm 200 \text{ nm}$  thick silicon dioxide top cladding layer with two metal layers for heaters: 1) heater filaments, and 2) heater contact pads. Finally, we will offer a top cladding opening performed by a silicon dioxide etch.

The schematic description of the process flow is given below:

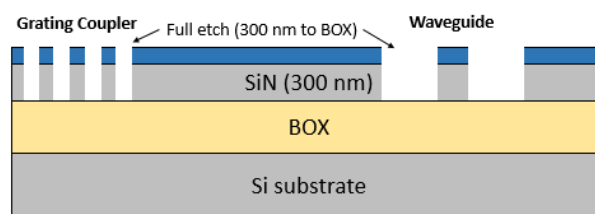
1. Starting SiNOI substrate



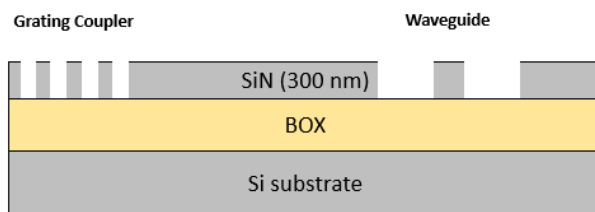
2. Resist patterning for SiN Etch (GDS layers 203 & 204) – 300 nm etch to BOX



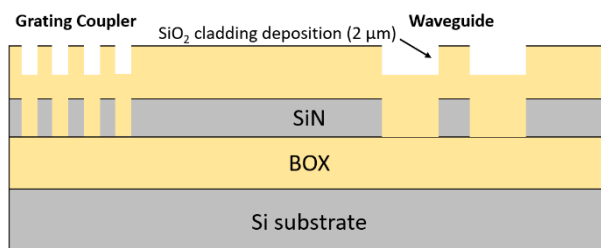
3. SiN etch (300 nm etch to BOX)



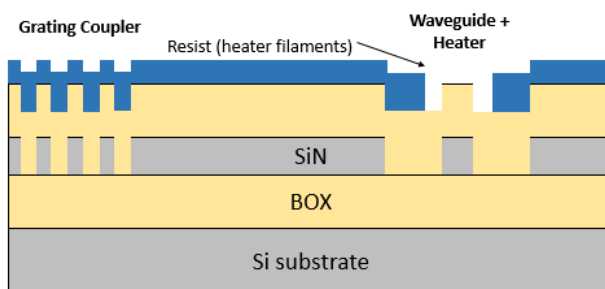
4. Resist strip



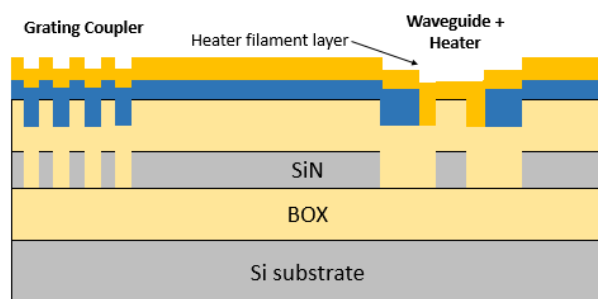
5. Silicon dioxide cladding deposition – 2 μm



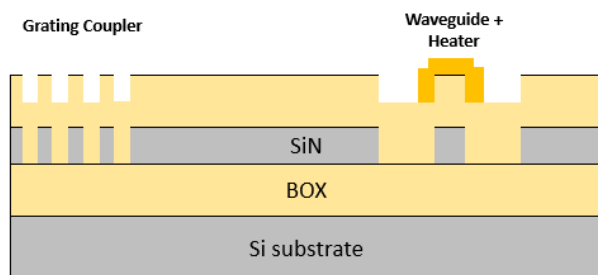
6. Resist patterning for Heater Filaments (GDS layer 39)



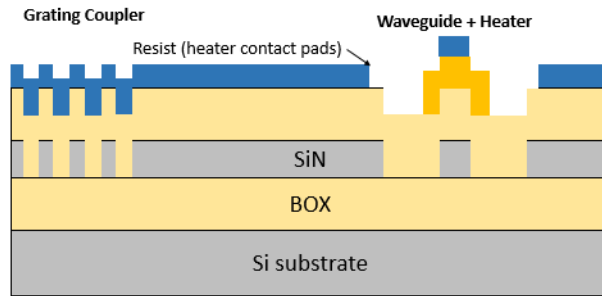
7. Heater filament deposition



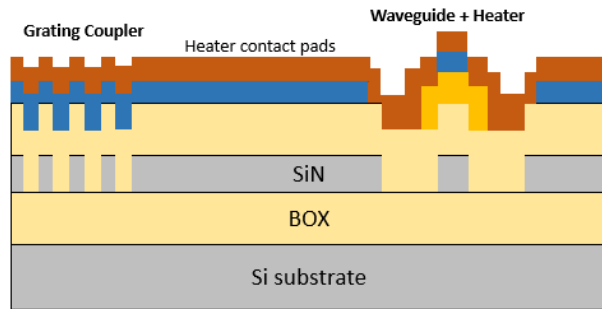
8. Metal lift-off



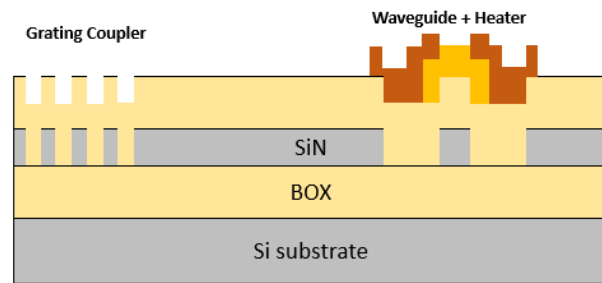
9. Resist patterning for Heater Contact Pads (GDS layer 41)



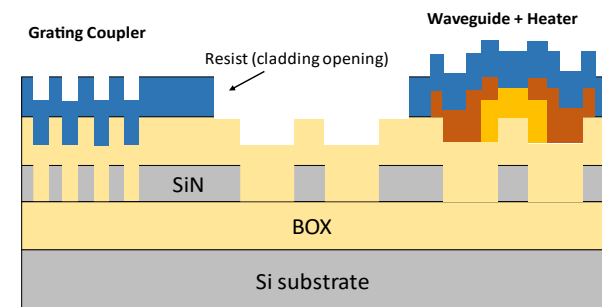
10. Heater contact pads deposition



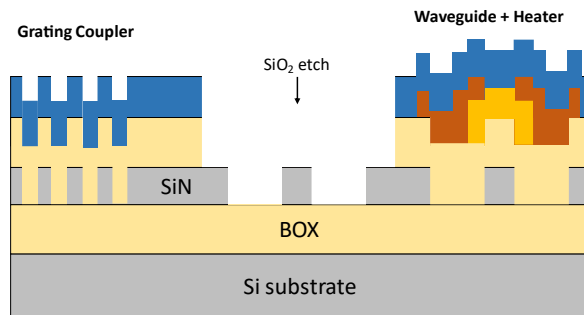
11. Metal lift-off



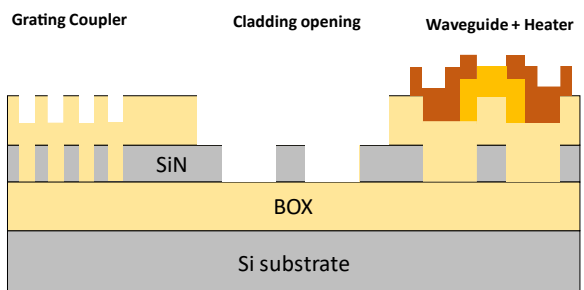
12. Resist patterning for cladding opening window (GDS Layer 22)



### 13. Silicon dioxide etch – 2 μm



### 14. Resist Strip



If you require any alternative processing steps (e.g. custom etch depths), we may be able to perform them for a suitable charge. Email [cornerstone@soton.ac.uk](mailto:cornerstone@soton.ac.uk) with your request.

## 5 DESIGN RULES

It is important that designs conform to the following design rules to ensure clarity and correct processing.

### 5.1 DESIGN AREA

The standard user cell has dimensions of **11.47 x 15.45 mm<sup>2</sup>**.

#### 5.1.1 PHYSICAL DIE SIZE

The physical size of the dies you will receive is approximately 16.5 x 12.5 mm<sup>2</sup>. This area includes a border the CORNERSTONE team will add that contains alignment marks, metrology boxes etc. If you require specific physical die dimensions, for example if integration to a PCB is required, please specify the physical die dimensions you require in the online mask submission form you are required to complete as part of the submission process (see Section 8).

## 5.2 GDS LAYERS

Each lithographic step in the fabrication process flow is identified by a specific GDS layer/s. These are as follows:

- Silicon Nitride Etch 1: 300 nm full etch to BOX – GDS Layer 203 (Light field): Drawn objects on this layer will be protected from the silicon nitride etch. Users should draw the waveguides and any other features to remain following the full silicon nitride etching. During fracturing processing, this will be translated into a pattern that defines 5  $\mu\text{m}$  wide trenches on either side of the waveguides drawn in GDS layer 203 (see Figure 1).

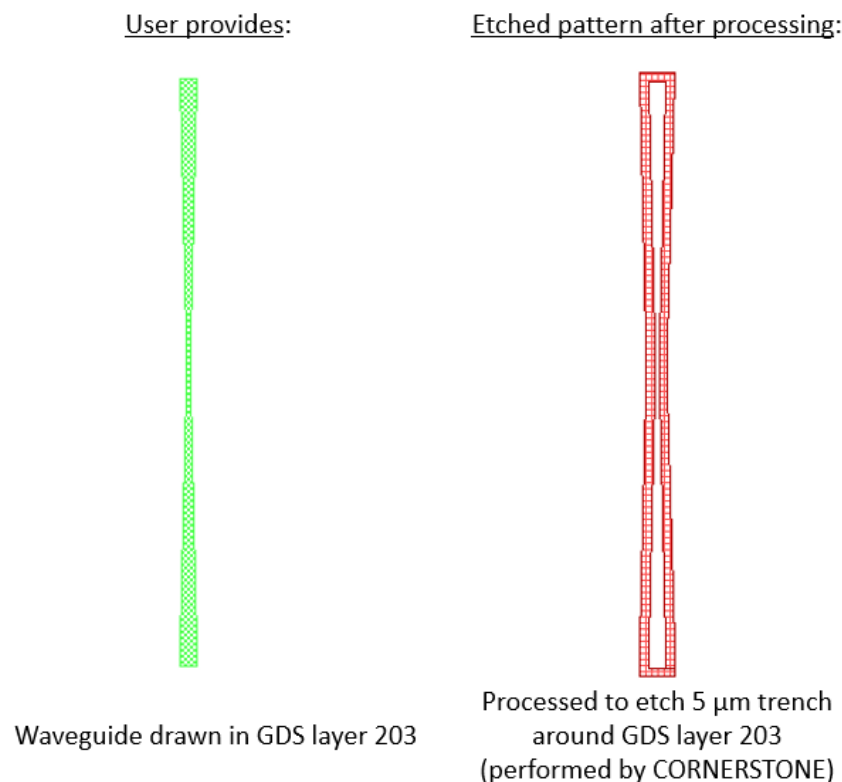


Figure 1 - Description of GDS Layer 203 processing.

If you require waveguide trenches that are a different width, refer to the guidelines for generating the trenches in Section 9. You can complete these steps yourself and modify the growth function dimension in step 1.

- Silicon Nitride Etch 1: 300 nm full etch to BOX – GDS Layer 204 (Dark field): Drawn objects on this layer will be exposed to the silicon nitride full etch to the BOX. An example photonic crystal structure is shown in Figure 2. The important thing to note here is that the waveguide layer drawn in GDS layer 203 should overlap the structures drawn in GDS layer 204, so that when the 5  $\mu\text{m}$  trenches are generated by CORNERSTONE, a continuous waveguide remains. Note that the client should

contact CORNERSTONE team if the design has photonic crystal structures with a diameter smaller than 600 nm to decide on whether structures need to be biased.

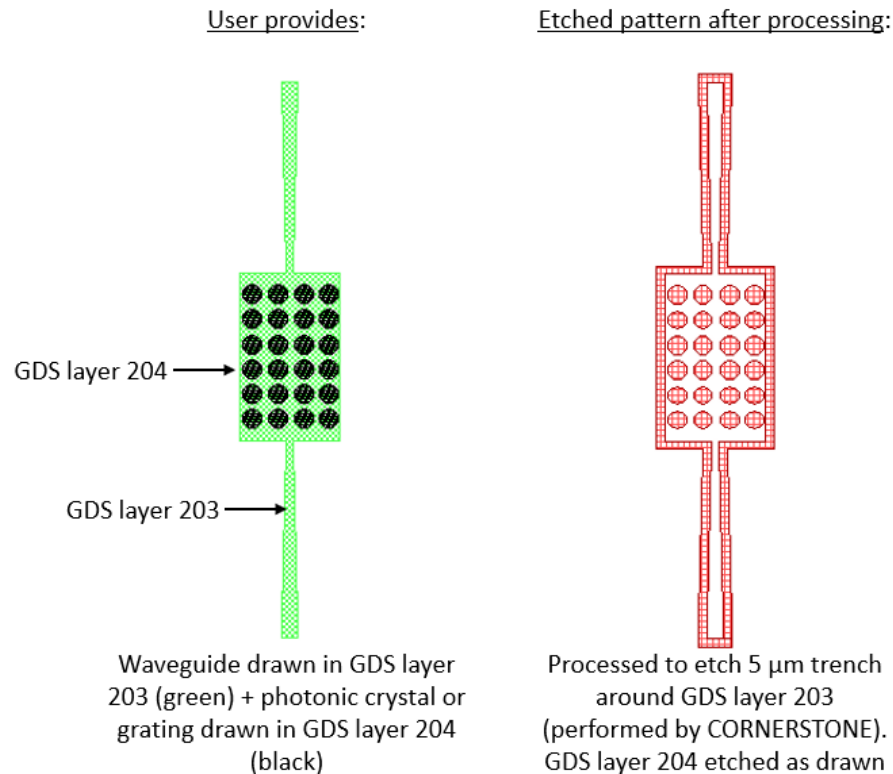


Figure 2 – Example photonic crystal structure using GDS Layers 203 & 204.

- Heater Filaments – GDS Layer 39 (Light field): This layer defines the heater filaments. Drawn objects on this layer will remain after metal lift-off. It is recommended to use a filament width of 900 nm for the best compromise between heater power efficiency, phase tunability and robustness.
- Heater Contact Pads – GDS Layer 41 (Light field): This layer defines the heater contact pads. Drawn objects on this layer will remain after metal lift-off. An example heater layout for a straight waveguide is included in the .gdsII template file. The contact pads can be modified according to your probe design.
- Cladding opening window – GDS Layer 22: This layer defines the area for oxide cladding etching. Drawn objects in this layer will be etched.
- Cell Outline – GDS Layer 99: This layer defines the design space boundaries (11.47 x 15.45 mm<sup>2</sup>).
- Labels – GDS Layer 100: This layer defines text labels, which will be merged with Silicon Nitride Etch 1 layer by the CORNERSTONE team. This layer will not have any design rule checking (DRC) performed.



Note: You do not need to add fabrication alignment marks to your design. Layer-to-layer alignment marks will be added by the CORNERSTONE team, placed outside the design area.

### 5.3 MINIMUM FEATURE SIZES, TARGET CRITICAL DIMENSIONS AND OTHER DESIGN RULES

- Minimum feature sizes, minimum gaps, and maximum feature widths for each GDS layer are detailed in Table .
- The target critical dimension for each GDS layer is listed in Table . Note that other feature sizes may have a small dimensional bias.
- A minimum spacing between waveguides of at least 10  $\mu\text{m}$  is recommended to avoid power coupling.
- An overlap of at least 2  $\mu\text{m}$  between GDS layer 39 (Heater Filaments) and GDS layer 41 (Heater Contact Pads) is recommended for optimal heater performance.
- Minimum size for a cladding opening should be at least 20 x 20  $\mu\text{m}^2$ .
- The client should contact CORNERSTONE team if GDS Layer 204 has photonic crystals structures with a diameter smaller than 600 nm to decide on whether structures need to be biased.

### 5.4 DESIGN RULES SUMMARY

A summary of the design rules and GDS layer numbers described in this section is detailed in below.

Table 2 – Design rules summary.

Layer description	GDS number	Field	Min. feature size	Min. gap	Max. feature length	Target lithography critical dimension
Silicon Nitride Etch 1 (300 nm full etch to BOX)*	203	Light	250 nm	250 nm	20 $\mu\text{m}$	660 nm
			350 nm	250 nm	N/a	
	204	Dark	250 nm	250 nm	20 $\mu\text{m}$	
			250 nm	350 nm	N/a	
Heater Filaments	39	Light	600 nm	10 $\mu\text{m}$	N/a	900 nm
Heater Contact Pads	41	Light	2 $\mu\text{m}$	10 $\mu\text{m}$	N/a	2 $\mu\text{m}$
Cladding opening window	22	Dark	20 $\mu\text{m}$	20 $\mu\text{m}$	N/a	20 $\mu\text{m}$
Cell Outline	99	N/a	N/a	N/a	N/a	N/a
Labels†	100	Dark	250 nm	250 nm	N/a	N/a

\*For the waveguide layer there is a maximum feature length restriction of 20  $\mu\text{m}$  when the minimum feature is 250 nm. This is because resist features that are long and thin can collapse during the development process. Resist widths of > 350 nm are stable and therefore there are no length restrictions for widths > 350 nm.

†Features drawn in the Labels layer will be merged into the Silicon Nitride Etch 1 layer by the CORNERSTONE team.

In order to help you ensure that you comply with the design rules, you can download and execute the KLayout pre-DRC script provided by CORNERSTONE on our website [www.cornerstone.sotonfab.co.uk/design-rules](http://www.cornerstone.sotonfab.co.uk/design-rules) (note that the automatic DRC will not check all of the design rules, so it remains very important to read the design rules in detail).

For users choosing the Priority option, it is essential to provide DRC-free mask layouts on or before the submission deadline. Therefore, users planning to initiate a priority batch should run the L-edit DRC file and confirm that the submitted design is free of design rule issues before the submission deadline. The CORNERSTONE team will not undertake post-submission DRC for Priority Access users to shorten the delivery timeline.

MPW users will have an opportunity to attend 1-to-1 Drop-in Session to pre-review mask layouts before the submission deadline, using the [link](#) to book a 20-min session.

## 5.5 FILE FORMAT

Designs must be submitted in a Graphical Database System file (extension *.gdsII*) or Open Artwork System Interchange Standard (extension *.oas*) format. Ensure a manufacturing grid size of 1 nm is used, as per the CORNERSTONE GDSII Template file.

We recommend dedicated lithography editing software be used in the design of the *.gdsII* or *.oas* file.

## 5.6 GDSII TEMPLATE FILE

A *.gdsII* template file has been made available on our website containing the information described in this section. Ensure that all submitted designs fit within the specified area, and that only the designated GDS layer numbers are used.

## 6 MATERIAL PROPERTIES

The measured refractive index of the LPCVD silicon nitride layer is shown in Figure 3 below. This data is also available in tabular format on our website.

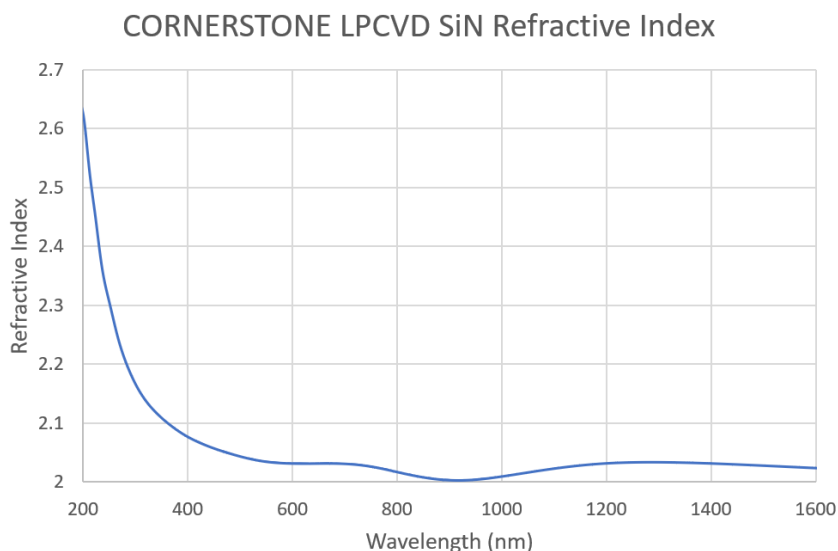


Figure 3 – Silicon nitride refractive index.

## 7 QUALITY ASSESSMENT

This fabrication run will be qualified by characterising a standard test pattern that is included on the chip (not part of the user cell). The test structures that will be checked after fabrication are reported in Table 3, together with the values that are targeted by the CORNERSTONE platform.

Table 3 – Quality assessment parameters.

Test structure	Parameter	Value
Straight single mode strip waveguide	Propagation loss	< 0.6 dB/cm for TE mode in C-band
MZI integrated with the PDK heater	Phase shift efficiency	< 175 mW/ $\pi$ phase shift

## 8 MASK SUBMISSION PROCEDURE

In order to be eligible to submit a design you must first sign-up to this call using the online form found using the link below. This is in order to enable us to prepare the necessary paperwork and plan the fabrication process effectively. The sign-up deadline is found at the top of this document.

[www.cornerstone.sotonfab.co.uk/home/mpw-sign-up-form](http://www.cornerstone.sotonfab.co.uk/home/mpw-sign-up-form)

Under no circumstances will we accept any design submissions for which we have not received a sign-up form.

After completing the sign-up form, when you are ready to submit your mask design on or before the mask submission deadline listed at the top of this document, follow the link below to the CORNERSTONE website mask submission page:

[www.cornerstone.sotonfab.co.uk/gds-file-upload](http://www.cornerstone.sotonfab.co.uk/gds-file-upload)

A purchase order (PO) must be uploaded to this form to pay the access fee. Purchase orders will not be accepted via email.

You must also upload your design file to the submission form. Ensure that the top cell in your design file is titled 'Cell0\_[Name of Institution]'.

For information about setting up CORNERSTONE as a supplier to your institution, or if you encounter any problems with the online forms, please contact [cornerstone@soton.ac.uk](mailto:cornerstone@soton.ac.uk).

## 9 MASK PROCESSING PERFORMED BY CORNERSTONE

Upon receipt of your .gdsII file, the CORNERSTONE team will perform the following mask processing steps in order to produce the final mask, based on the descriptions provided in Section 5.2.

Silicon Nitride Etch 1 GDS 203 (Light field) – waveguides & GDS Layer 204 (Dark field) – gratings:

1. Grow Waveguide layer (GDS layer 203) by 5  $\mu\text{m}$  in all directions.
2. Subtract the Waveguide layer (GDS layer 203) from the output of (1) to produce the etch trenches around the drawn waveguides.
3. Merge the output of (2) with the dark field Silicon Nitride Etch layer (GDS layer 204) and the Labels layer (GDS layer 100).

## 10 TECHNICAL SUPPORT

If you have any questions relating to the fabrication process or design rules, please contact the CORNERSTONE team ([cornerstone@soton.ac.uk](mailto:cornerstone@soton.ac.uk)).

## 11 DEVICE DELIVERY

A total of 10 replica cells will be delivered to each user. The delivery time schedule can be found in Table 1.

## 12 FEEDBACK

Feedback is essential to the CORNERSTONE team. It is required to ensure a continuous improvement to the quality of our services. It is also evidence on the user satisfaction, and a measure to what extent we were able to meet user requirements. Therefore, we kindly ask our users to provide feedback to us, including device performance data, SEM images, future interests for the CORNERSTONE project etc. A feedback form will be sent to you along with your chips.

Alternatively, email [cornerstone@soton.ac.uk](mailto:cornerstone@soton.ac.uk) with your comments.

## 13 PUBLICATIONS

If you are benefitting from subsidised access via the C-PIC funding, please include the following statement in the “Funding” section of any publications:

“The chip fabrication for this research was funded by the Engineering and Physical Sciences Research Council (EPSRC) C-PIC (EP/Z531066/1) project.”

This is important to us to be able to demonstrate impact from the funding.

If you are a paying user, we kindly ask that you include CORNERSTONE in the “Acknowledgments” section of any publications that result from the chips you receive from CORNERSTONE.